

Fig. 1

Laver		Mole	Fraction	Strain	PL	Thickness	۸۵	Level	fvna	Dopant
	Material	(start)		%	(mu)	(mm)	(start)	(finish)	3 PC	
	GaAs				cab	0.005	>2e19		d	Zn
3 5	Al(x)GaAs	0.5		0	***		>2e19		d	Zn
•					(see below)					
10	GaAs					0.1	>2e19		Q	Zn
T	Al(x)GaAs	0.32	0.0			0.12	2e18		þ	Zn
	Al(x)GaAs					1.7	2e18		ď	Zn
	AI(x)GaAs	0.32					2e17	2e18	р	Zn
	Al(x)GaAs	0.1	0.32		0.11	0.11			p/n	U/d
	GaIn(x)As	0.17		1.79	970 nm	0.008			P/N	p/n
	Al(x)GaAs		0.1	ļ		0.11			D/Q	n/d
	Al(x)GaAs	0.32					2e18		_	Silicon
	Al(x)GaAs		0.32				2e18		C	Silicon
	GaAs						2e18		2	Silicon

Fig. 2

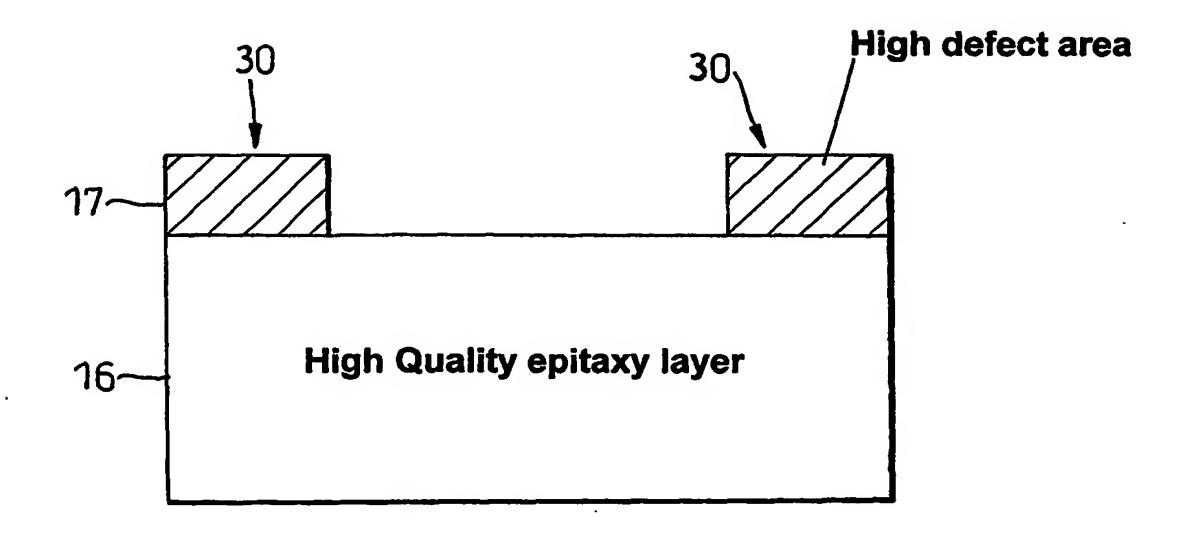


Fig. 3

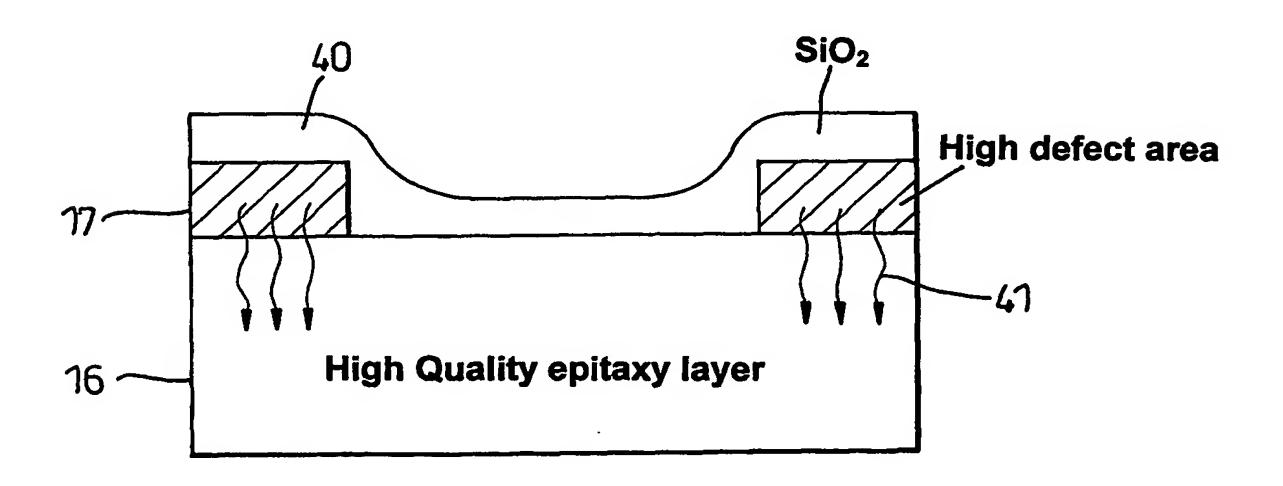


Fig. 4

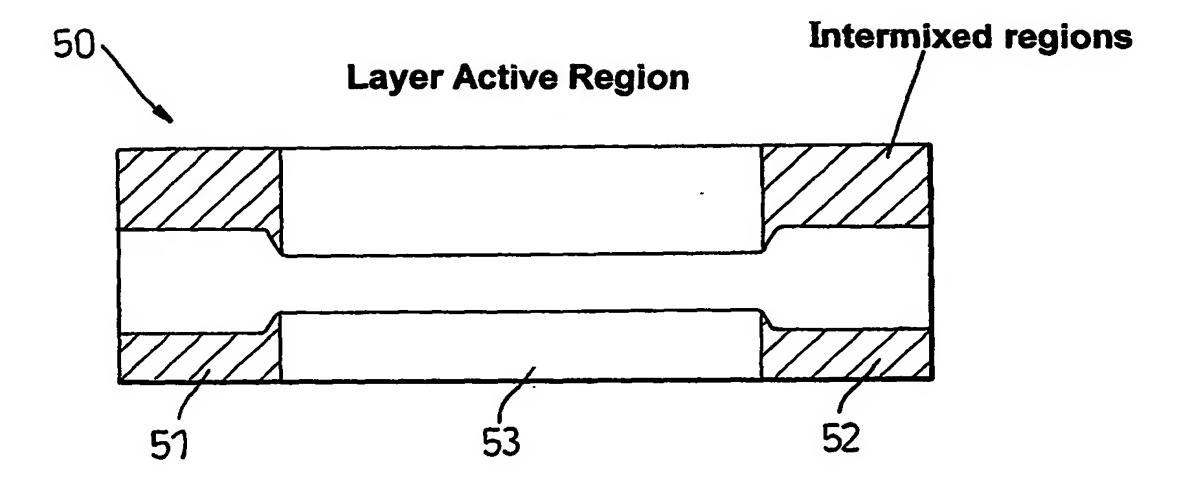


Fig. 5

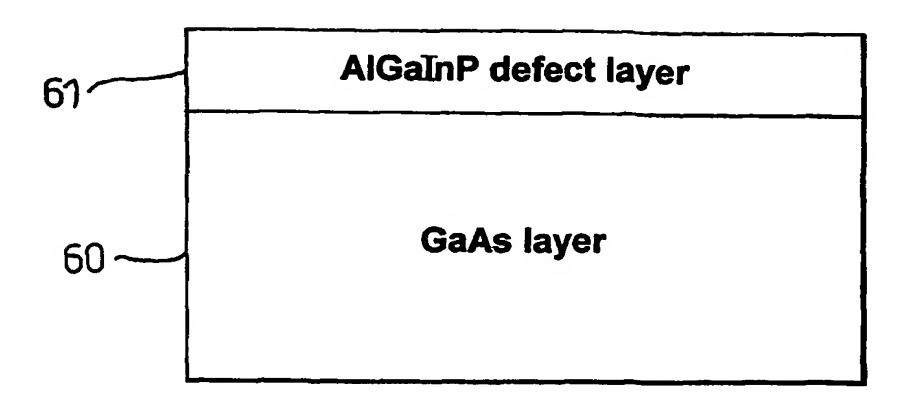


Fig. 6

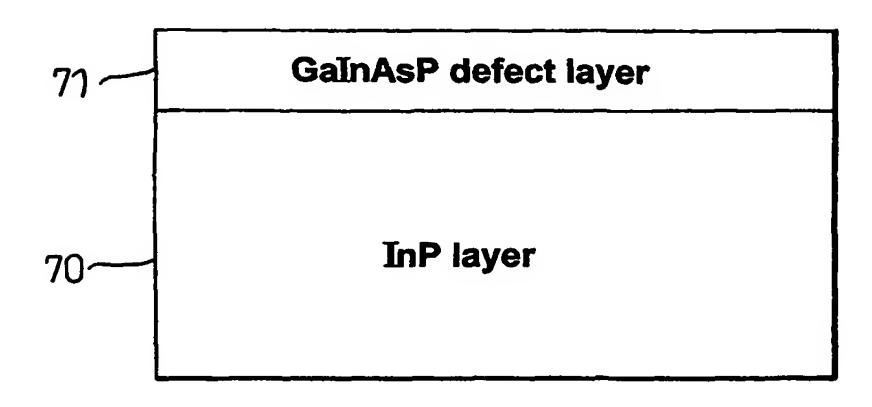
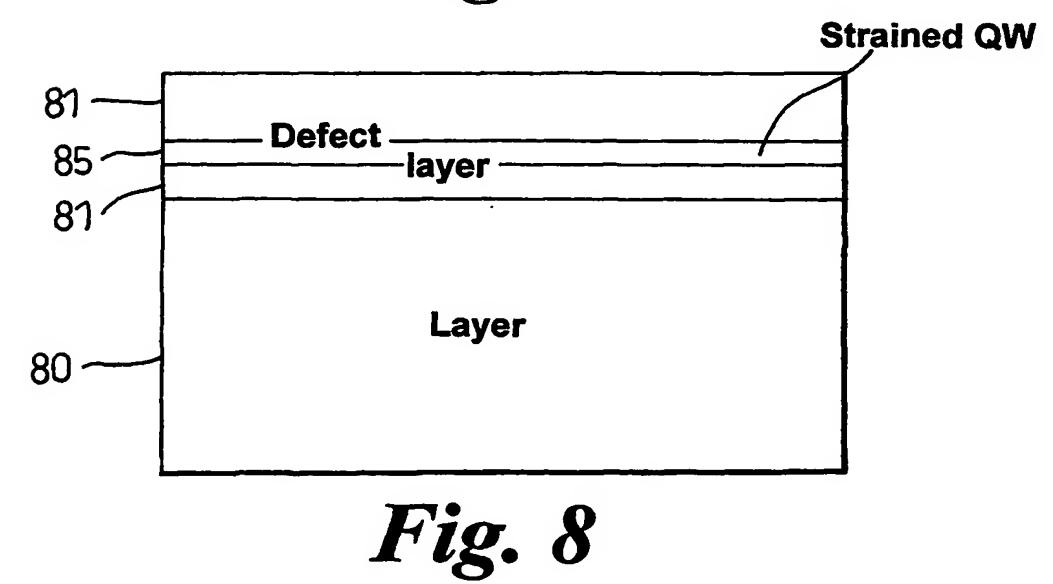
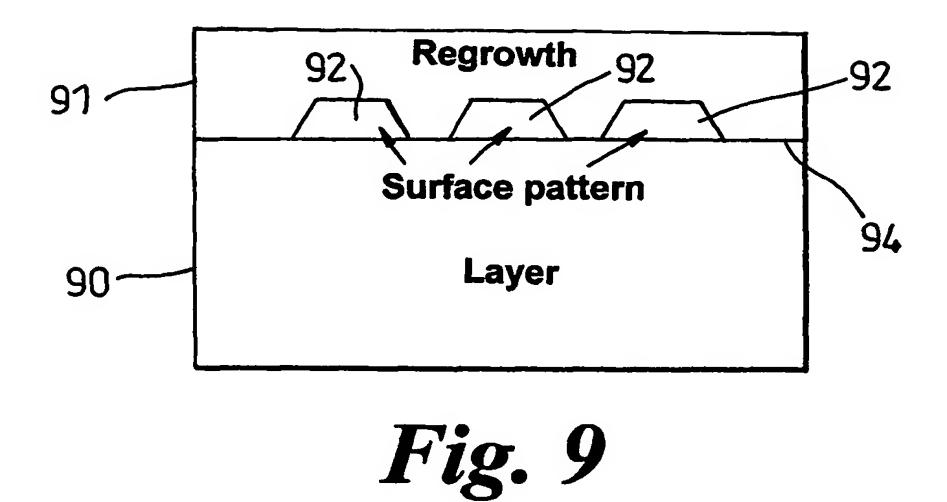
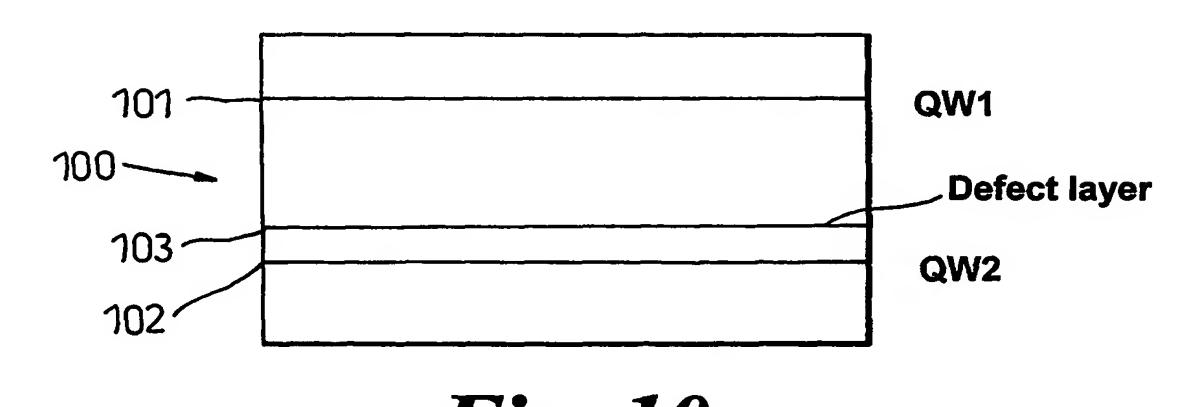


Fig. 7



SUBSTITUTE SHEET (RULE 26)





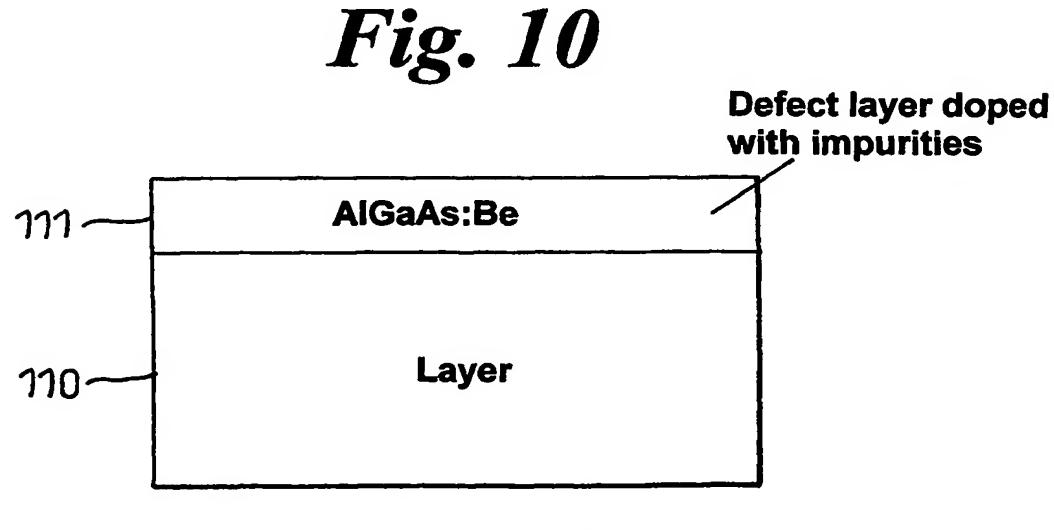


Fig. 11

SUBSTITUTE SHEET (RULE 26)

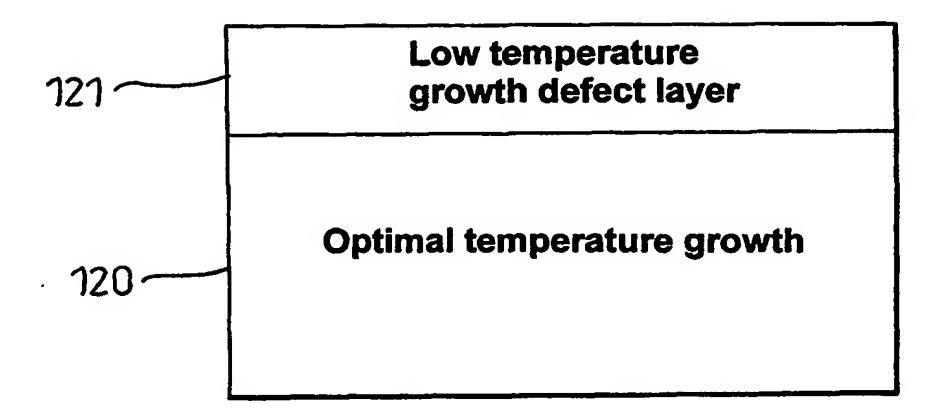


Fig. 12